IN THE SUBSTITUTE SPECIFICATION:

Page 3, amend the paragraph beginning on line 18 to read as follows:

Fig. 5 shows a crystal structure of a ruthenium cyclopentadienyl complex used in accordance with this invention. σ or π bonds are present between a 5 ~~cyclic~~ membered ring and ruthenium metal, and a temperature at 180°C or higher is necessary as the energy of dissociation in view of the bonding energy. Further, the adhesion rate of the complex is constant on a Si substrate within a temperature range from 180°C or higher and 250°C or lower, and decomposition - adhesion on the surface proceeds preferentially at a higher temperature.

B1

Page 5, amend the paragraph beginning on line 5 to read as follows:

Fig. 2 shows a crystal structure of a ruthenium β-diketone complex used in accordance with this invention. π bonds are present between oxygen in a 6 ~~cyclic~~ membered ring and ruthenium metal and can dissociate at a temperature of 300°C or higher in view of the bond energy. However, since dissociation of an oxygen - carbon bond or dissociation of an oxygen - ruthenium bond proceeds simultaneously. the adhesion rate is small and decomposition deposition near the surface proceeds preferentially. Further, at a temperature higher than 500°C, island crystals are formed due to violent decomposing reaction to result in a film quality that is not capable of attaining contact. Then, as shown in Fig. 3, a homogeneous electrode thin film comprising Ru, RuO_2 or a mixture of Ru and RuO_2 can be prepared on the surface, the bottom and the inside wall within a temperature range from 300°C or higher to 500°C or lower by an MOCVD process using a ruthenium ß-diketone complex on a structure having a three-dimensional configuration by constituting the structure having a three-

B2

dimensional configuration with an insulation layer consisting of a dual layered structure comprising a surface layer 31 having a small adhesion rate and a side wall layer 32 having a large adhesion rate, for example, MgO/SiO_2 or Al_2O_3/SiO_2 for the electrode material.

B2

Page 18, amend the paragraph beginning on line 7 to read as follows:

In addition to the discyclopentadienyl ruthenium complex in which R = H, homogeneous thin Ru films could be formed as the bottom electrode and the top electrode by the same method as described above also in a case of using ~~dis(methylcyclopentadienyl)~~ bis(methylcyclopentadienyl) ruthenium at R = CH_3, ~~dis(ethylcyclopentadienyl)~~ bis(ethylcyclopentadienyl) ruthenium at R = C_2H_5, ~~dis(propylcyclopentadienyl)~~ bis(propylcyclopentadienyl) ruthenium at R = C_3H_7, ~~dis(butylclopentadienyl)~~ bis(butylcyclopentadienyl) ruthenium at R = C_4H_9.

B3

Page 21, amend the paragraph beginning on line 18 to read as follows:

Homogeneous Ru thin films could be formed on the bottom electrode and the top electrode by the same method as described above also in a case of using acetylacetonate ruthenium at ~~R~~ R' = CH_3 and hexafluoroacetyl acetonate ruthenium at ~~R~~ R' = CF_3 in addition to the dibivaloylmethanate ruthenium complex at ~~R~~ R' = C $(CH_3)_3$.

B4